Jacopo Frascaroli

List of Publications by Year in descending order

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687363 752698 23 593 13 20 citations h-index g-index papers 23 23 23 903 docs citations times ranked citing authors all docs

#	Article	IF	CITATIONS
1	Resistive random access memory (RRAM) technology: From material, device, selector, 3D integration to bottom-up fabrication. Journal of Electroceramics, 2017, 39, 21-38.	2.0	79
2	Role of metal-oxide interfaces in the multiple resistance switching regimes of Pt/HfO2/TiN devices. Applied Physics Letters, $2015,107,.$	3.3	78
3	Resistive Switching in High-Density Nanodevices Fabricated by Block Copolymer Self-Assembly. ACS Nano, 2015, 9, 2518-2529.	14.6	72
4	Evidence of soft bound behaviour in analogue memristive devices for neuromorphic computing. Scientific Reports, 2018, 8, 7178.	3.3	54
5	Effect of Al doping on the retention behavior of HfO2 resistive switching memories. Microelectronic Engineering, 2015, 147, 104-107.	2.4	52
6	Role of Al doping in the filament disruption in HfO ₂ resistance switches. Nanotechnology, 2017, 28, 395202.	2.6	36
7	Thermodynamic stability of high phosphorus concentration in silicon nanostructures. Nanoscale, 2015, 7, 14469-14475.	5.6	33
8	Extended memory lifetime in spiking neural networks employing memristive synapses with nonlinear conductance dynamics. Nanotechnology, 2019, 30, 015102.	2.6	33
9	Ozone-Based Sequential Infiltration Synthesis of Al ₂ O ₃ Nanostructures in Symmetric Block Copolymer. ACS Applied Materials & Symmetric Block Copolymer.	8.0	29
10	Quantification of phosphorus diffusion and incorporation in silicon nanocrystals embedded in silicon oxide. Surface and Interface Analysis, 2014, 46, 393-396.	1.8	26
11	Spike-driven threshold-based learning with memristive synapses and neuromorphic silicon neurons. Journal Physics D: Applied Physics, 2018, 51, 344003.	2.8	23
12	Stimulated Ionic Telegraph Noise in Filamentary Memristive Devices. Scientific Reports, 2019, 9, 6310.	3.3	20
13	(Invited) Analog HfO2-RRAM Switches for Neural Networks. ECS Transactions, 2017, 75, 85-94.	0.5	15
14	Surface passivation for ultrathin Al ₂ O ₃ layers grown at low temperature by thermal atomic layer deposition. Physica Status Solidi (A) Applications and Materials Science, 2013, 210, 732-736.	1.8	13
15	Fabrication of periodic arrays of metallic nanoparticles by block copolymer templates on HfO ₂ substrates. Nanotechnology, 2015, 26, 215301.	2.6	11
16	Modeling of phosphorus diffusion in silicon oxide and incorporation in silicon nanocrystals. Journal of Materials Chemistry C, 2016, 4, 3531-3539.	5.5	10
17	Automatic Defect Detection in Epitaxial Layers by Micro Photoluminescence Imaging. IEEE Transactions on Semiconductor Manufacturing, 2022, 35, 540-545.	1.7	3
18	Electrical AFM for the Analysis of Resistive Switching. Nanoscience and Technology, 2019, , 205-229.	1.5	2

#	Article	IF	CITATIONS
19	Internal and External Gettering of Iron Contamination in Power Technologies. Physica Status Solidi (A) Applications and Materials Science, 2021, 218, 2100206.	1.8	2
20	(Invited) Impact of the Substrate Specifications on the Extended Defects Induced by the Deep Trench Isolation. ECS Transactions, 2021, 102, 29-36.	0.5	1
21	Resistive Random Access Memory (RRAM) Technology: From Material, Device, Selector, 3D Integration to Bottom-Up Fabrication. Kluwer International Series in Electronic Materials: Science and Technology, 2022, , 33-64.	0.5	1
22	Hafnium Impurity Defects in Silicon: A Characterization. ECS Journal of Solid State Science and Technology, 2018, 7, P583-P587.	1.8	0
23	Microâ€photoluminescence imaging at room temperature of crystallographic defects generated by deep trench structures. Physica Status Solidi (A) Applications and Materials Science, 0, , .	1.8	0